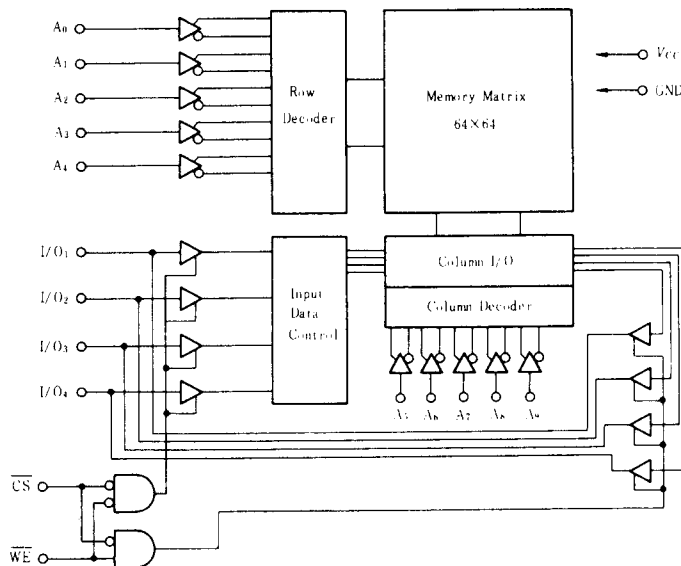


HM472114-3, HM472114-4, HM472114P-3, HM472114P-4

1024-word × 4-bit Static Random Access Memory

- Fast Access Time HM472114-3 300ns (max.)
HM472114-4 450ns (max.)
- Low Operating Power 200mW (typ)
- Single +5V Supply Voltage
- Completely Static Memory No Clock or Refresh Required
- Directly TTL Compatible All Inputs and Outputs
- Common Data Inputs and Output
- Three-state Outputs
- DC Standby Mode Reduces V_{CC}
- N-channel Si Gate MOS Technology
- Interchangeable with Intel 2114L Series

■ BLOCK DIAGRAM

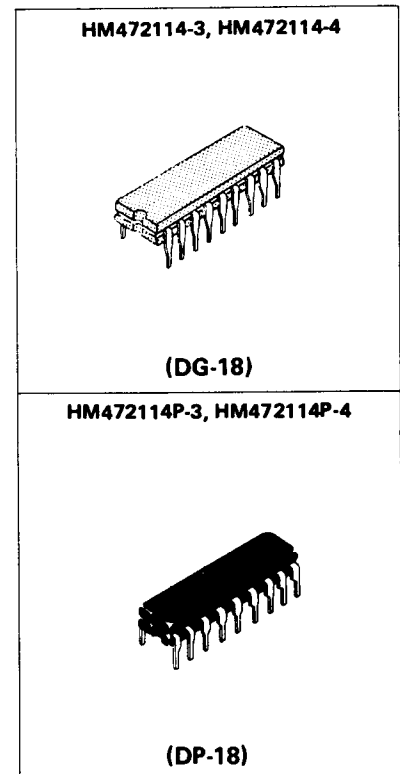


■ ABSOLUTE MAXIMUM RATINGS

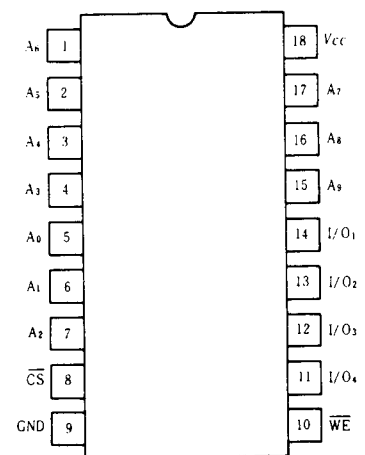
| Item | Symbol | Value | Unit |
|-------------------------------|-----------|-------------|------|
| Terminal Voltage | V_T | -0.3 to +7 | V |
| Power Dissipation | P_T | 1.0 | W |
| Operating Temperature | T_{opr} | 0 to +70 | °C |
| Storage Temperature (Ceramic) | T_{stg} | -65 to +150 | °C |
| Storage Temperature (Plastic) | T_{stg} | -55 to +125 | °C |

■ RECOMMENDED DC OPERATING CONDITIONS

| Item | Symbol | min. | typ. | max. | Unit |
|-----------------------|-----------|------|------|----------------|------|
| Supply Voltage | V_{CC} | 4.5 | 5.0 | 5.5 | V |
| Input Voltage | V_{IL} | -0.3 | — | 0.8 | V |
| | V_{IH} | 2.0 | — | $V_{CC} + 1.0$ | V |
| Operating Temperature | T_{opr} | 0 | — | 70 | °C |



■ PIN ARRANGEMENT



(Top View)

■ DC AND OPERATING ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$, $T_a=0 \sim +70^\circ C$)

| Item | Symbol | Test Condition | min. | typ. | max. | Unit |
|-----------------------|------------|--|------|------|--------------|---------|
| Input Leakage Current | I_{LI} | $V_{in}=0 \sim 5.5V$ | — | — | 10 | μA |
| I/O Leakage Current | $ I_{LO} $ | $\overline{CS}=2.0V$, $V_{i/o}=0.4 \sim V_{CC}$ | — | — | 10 | μA |
| Supply Current | I_{CC} | $V_{in}=5.5V$, $I_{i/o}=0mA$ | — | 35 | 60 | mA |
| Input Voltage | V_{IL} | | -0.5 | — | 0.8 | V |
| | V_{IH} | | 2.0 | — | $V_{CC}+1.0$ | V |
| Output Voltage | V_{OL} | $I_{OL}=2.1mA$ | — | — | 0.4 | V |
| | V_{OH} | $I_{OH}=-0.6mA$, $V_{CC}=4.5V$ | 2.4 | — | — | V |
| | | $I_{OH}=-1.0mA$, $V_{CC}=4.75V$ | 2.4 | — | — | |

■ CAPACITANCE ($T_a=25^\circ C$, $f=1MHz$)

| Item | Symbol | Test Condition | min. | typ. | max. | Unit |
|-------------------|-----------|----------------|------|------|------|------|
| Input Capacitance | C_{in} | $V_{in}=0V$ | — | 3 | 5 | pF |
| I/O Capacitance | $C_{i/o}$ | $V_{i/o}=0V$ | — | 5 | 10 | pF |

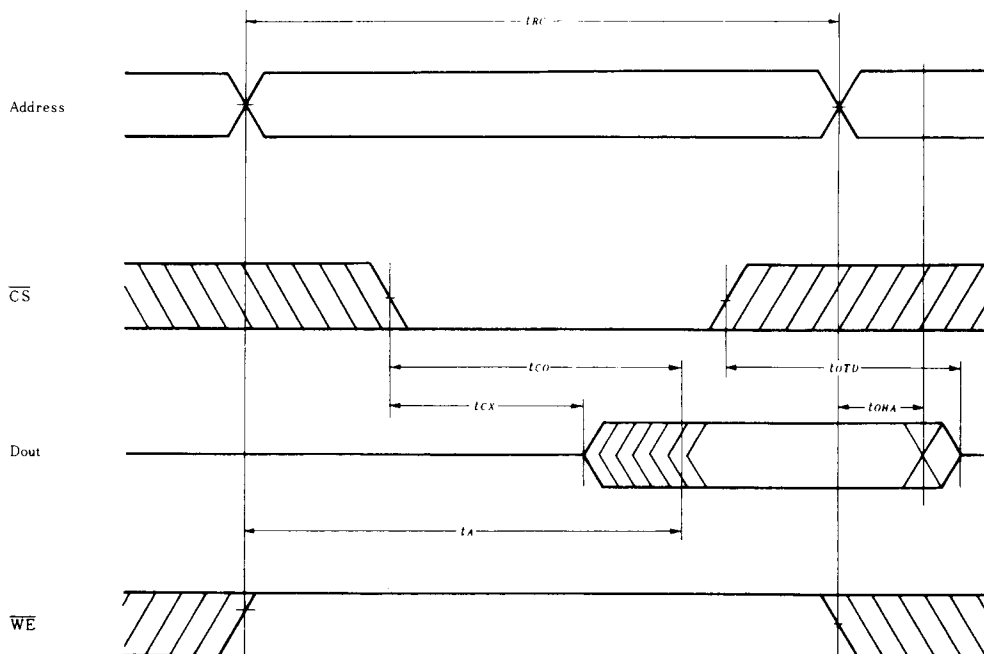
■ AC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$, $T_a=0$ to $+70^\circ C$)

● AC TEST CONDITIONS

| | |
|--------------------------------|---------------------|
| Input High Levels | 2.0V |
| Input Low Levels | 0.8V |
| Input Rise and Fall Times | 10ns |
| Input and Output Timing Levels | 1.5V |
| Output Load | 1 TTL + $C_L=100pF$ |

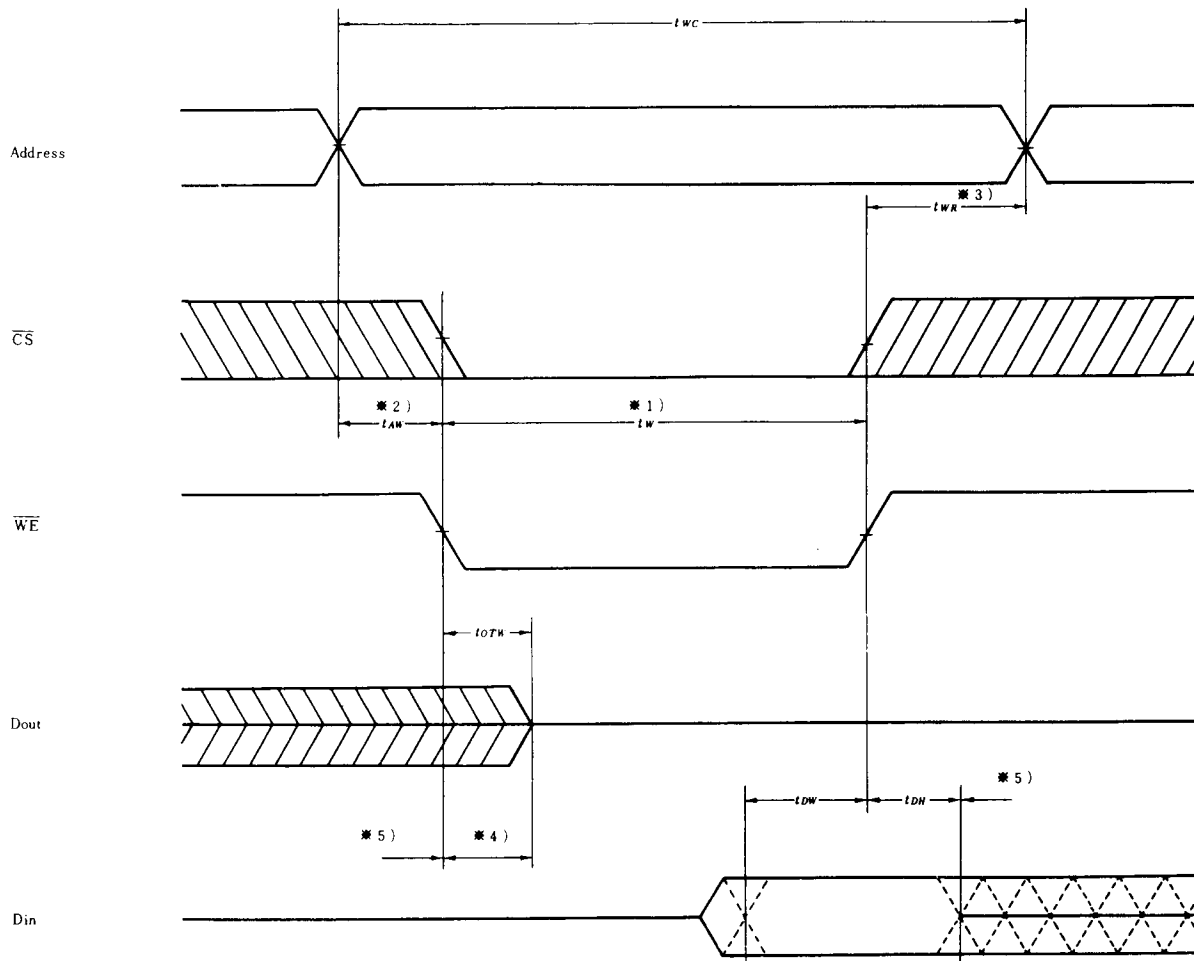
● READ CYCLE

| Item | Symbol | HM472114-3, HM472114P-3 | | HM472114-4, HM472114P-4 | | Unit |
|-----------------------------------|-----------|-------------------------|------|-------------------------|------|------|
| | | min. | max. | min. | max. | |
| Read Cycle Time | t_{RC} | 300 | — | 450 | — | ns |
| Access Time | t_A | — | 300 | — | 450 | ns |
| \overline{CS} -to-Output Valid | t_{CO} | — | 100 | — | 120 | ns |
| \overline{CS} -to-Output Active | t_{CX} | 20 | — | 20 | — | ns |
| Output 3-state from Deselection | t_{OTD} | — | 80 | — | 100 | ns |
| Output Hold from Address Change | t_{OHA} | 50 | — | 50 | — | ns |



■ WRITE CYCLE

| Item | Symbol | HM472114-3, HM472114P-3 | | HM472114-4, HM472114P-4 | | Unit |
|-----------------------------|-----------|-------------------------|------|-------------------------|------|------|
| | | min. | max. | min. | max. | |
| Write Cycle Time | t_{WC} | 300 | — | 450 | — | ns |
| Address to Write Setup Time | t_{AW} | 20 | — | 50 | — | ns |
| Write Pulse Width | t_W | 150 | — | 200 | — | ns |
| Write Release Time | t_{WR} | 0 | — | 0 | — | ns |
| Output 3-state from Write | t_{OTW} | — | 80 | — | 100 | ns |
| Data-to-Write Time Overlap | t_{DW} | 150 | — | 200 | — | ns |
| Data Hold from Write Time | t_{DH} | 0 | — | 0 | — | ns |



- Notes:
- 1) \overline{CS} and \overline{WE} are paced in the WRITE state during low level period (t_W).
 - 2) t_{AW} is an interval from the address setting through fall of the pulse, \overline{CS} or \overline{WE} .
 - 3) t_W is from the earlier rise pulse of \overline{CS} or \overline{WE} till the end of the light cycle (t_{WC}).
 - 4) During this period the pulse is output so that the input signal which is the same in phase with the output may be applied to the I/O terminal.
 - 5) During this period, when the \overline{CS} signal is at low level, the pulse is output so that the input signal which is the same in phase with the output data may be applied, if required. Do not however apply the input signal of reverse phase.